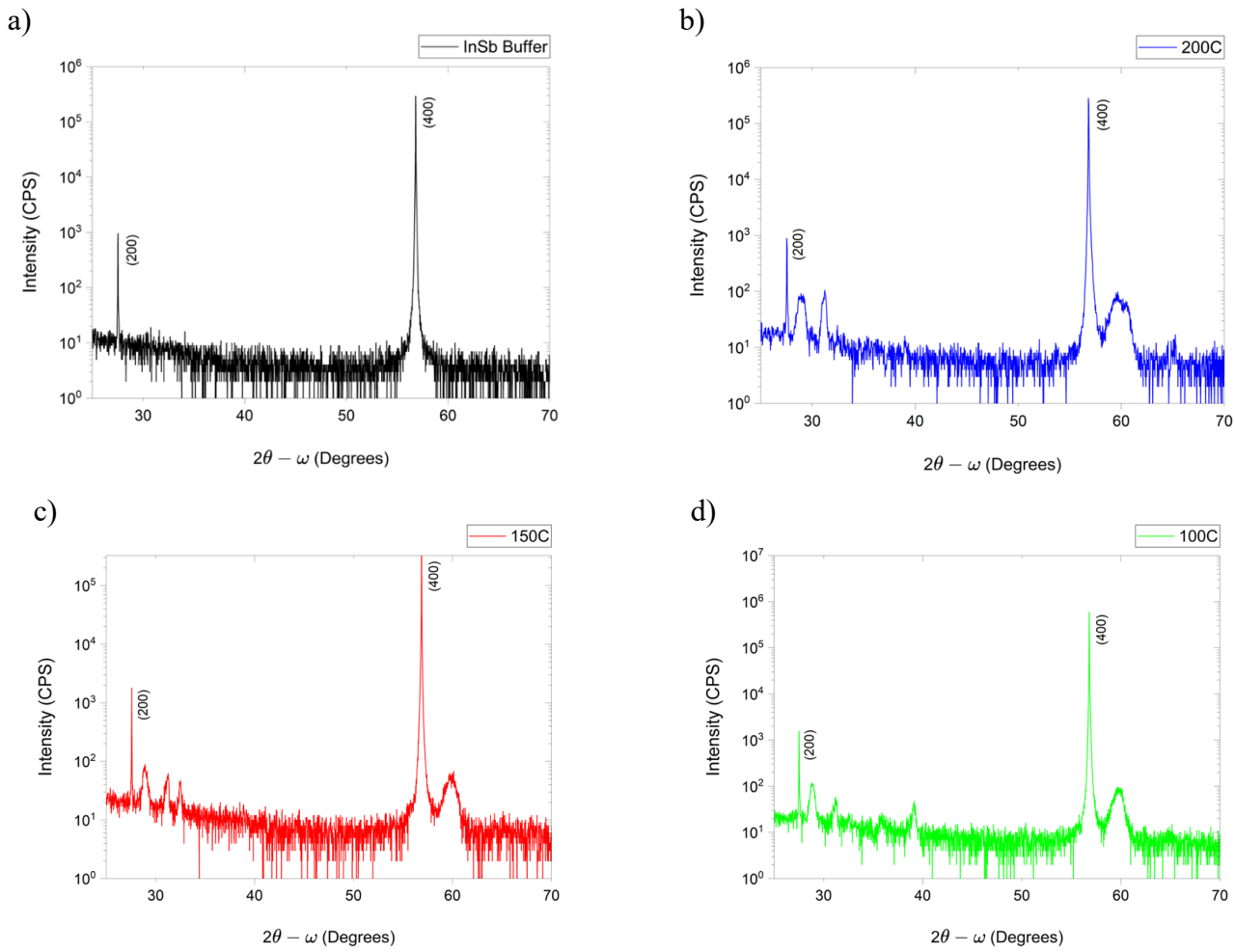

Figure 1: **(a)** 2θ-ω vs. Intensity x-ray diffraction scan of InSb(100) substrate with 200nm buffer layer. The peak at 27.51 degrees corresponds to the InSb(200) reflection, and the peak at 56.79 degrees corresponds to the InSb(400) reflection. **(b)** 2θ-ω vs. Intensity x-ray diffraction scan of InSb(100) substrate with 200nm buffer layer and GaBi film grown at 200C. The peak at 28.93 degrees corresponds to the GaBi(200) peak (FWHM 0.3597 degrees) and the peak at 59.79 degrees corresponds to the GaBi(400) peak (FWHM 0.0384 degrees). The peak at 31.2 degrees corresponds to the Bi(112) peak. **(c)** 2θ-ω vs. Intensity x-ray diffraction scan of InSb(100) substrate with 200nm buffer layer and GaBi film grown at 150C. The peak at 28.93 degrees corresponds to the GaBi(200) (FWHM 0.3597 degrees) reflection and the peak at 59.71 corresponds to the GaBi(400) reflection (FWHM 0.0384 degrees). The peak at 32.51 degrees is currently unidentified. **(d)** 2θ-ω vs. Intensity x-ray diffraction scan of InSb(100) substrate with 200nm buffer layer and GaBi film grown at 100C. The peak at 28.83 degrees corresponds to the GaBi(200) (FWHM 0.3641 degrees) reflection and the peak at 59.81 corresponds to the GaBi(400) reflection (FWHM 0.0426 degrees). The peak at 39.13 degrees is currently unidentified.